

# ALD1706A/ALD1706B ALD1706/ALD1706G

# ULTRA MICROPOWER RAIL-TO-RAIL CMOS OPERATIONAL AMPLIFIER

#### GENERAL DESCRIPTION

The ALD1706A/ALD1706B/ALD1706/ALD1706G is a monolithic CMOS ultra micropower high slew-rate, high performance operational amplifier intended for a broad range of analog applications using  $\pm 1$ V to  $\pm 5$ V dual power supply systems, as well as  $\pm 2$ V to  $\pm 10$ V battery operated systems. All device characteristics are specified for  $\pm 5$ V single supply or  $\pm 2.5$ V dual supply systems. Supply current is  $40\mu$ A maximum at 5V supply voltage. It is manufactured with Advanced Linear Devices' enhanced ACMOS silicon gate CMOS process.

The ALD1706A/ALD1706B/ALD1706/ALD1706G is designed to offer high performance for a wide range of applications requiring very low power dissipation. It has been developed specifically for the +5V single battery or  $\pm$ 1V to  $\pm$ 5V dual battery user and offers the popular industry standard single operational amplifier pin configuration.

Several important characteristics of the device make application easier to implement at those voltages. First, the operational amplifier can operate with rail to rail input and output voltages. This means the signal input voltage and output voltage can be close to or equal to the positive and negative supply voltages. This feature allows numerous analog serial stages and flexibility in input signal bias levels. Second, the device was designed to accommodate mixed applications where digital and analog circuits may operate off the same power supply or battery. Third, the output stage can typically drive up to 25pF capacitive and 20K $\Omega$  resistive loads. These features, combined with extremely low input currents, high open loop voltage gain of 100V/mV, useful bandwidth of 400KHz, a slew rate of 0.17V/µs, low offset voltage and temperature drift, make the ALD1706A/ALD1706B/ALD1706/ALD1706G a versatile, micropower operational amplifier.

The ALD1706A/ALD1706B/ALD1706/ALD1706G, designed and fabricated with silicon gate CMOS technology, offers 0.1 pA typical input bias current. On chip offset voltage trimming allows the device to be used without nulling in most applications. Additionally, robust design and rigorous screening make this device especially suitable for operation in temperature-extreme environments and rugged conditions.

# FEATURES

- All parameters specified for +5V single supply or ±2.5V dual supply systems
- Rail to rail input and output voltage ranges
- No frequency compensation required -unity gain stable
- Extremely low input bias currents --1.0pA typical (30pA max.)
- Ideal for high source impedance applications
- Dual power supply  $\pm 1.0V$  to  $\pm 5.0V$  operation
- Single power supply +2.0V to +10.0V operation
- High voltage gain -- typically 100V/mV @ ±2.5V(100dB)
- Drive as low as  $10K\Omega$  load
- · Output short circuit protected
- Unity gain bandwidth of 0.7MHz
- Slew rate of 0.7V/μs
- Low power dissipation
- Suitable for rugged, temperature-extreme environments

#### **APPLICATIONS**

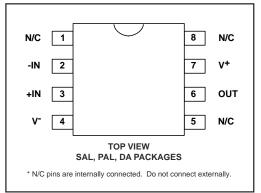
- Voltage amplifier
- Voltage follower/buffer
- Charge integrator
- Photodiode amplifier
- Data acquisition systems
- · High performance portable instruments
- Signal conditioning circuits
- Sensor and transducer amplifiers
- Low leakage amplifiers
- Active filters
- Sample/Hold amplifier
- Picoammeter
- · Current to voltage converter

#### **ORDERING INFORMATION** ("L" suffix denotes lead-free (RoHS))

Opera	Operating Temperature Range								
0°C to +70°C	0°C to +70°C	-55°C to 125°C							
8-Pin Small Outline Package (SOIC)	8-Pin Plastic Dip Package	8-Pin CERDIP Package							
ALD1706ASAL ALD1706BSAL ALD1706SAL ALD1706GSAL	ALD1706APAL ALD1706BPAL ALD1706PAL ALD1706GPAL	ALD1706ADA ALD1706BDA ALD1706DA							

\* Contact factory for leaded (non-RoHS) or high temperature versions.

# **PIN CONFIGURATION**



Rev 2.1 ©2010 Advanced Linear Devices, Inc. 415 Tasman Drive, Sunnyvale, CA 94089-1706 Tel: (408) 747-1155 Fax: (408) 747-1286 www.aldinc.com

# ABSOLUTE MAXIMUM RATINGS

Supply voltage, V+		10.6V
Differential input voltage range		-0.3V to V++0.3V
Power dissipation		600 mW
Operating temperature range	SAL, PAL packages	0°C to +70°C
	DA package	55°C to +125°C
Storage temperature range		65°C to +150°C
Lead temperature, 10 seconds	3	+260°C
CALITION - ESD Sensitive Dev	vice. Use static control procedures in FSD controlled environment	

CAUTION: ESD Sensitive Device. Use static control procedures in ESD controlled environment.

# OPERATING ELECTRICAL CHARACTERISTICS $T_A = 25^{\circ}C \ V_S = \pm 2.5 V$ unless otherwise specified

			1706A	1		1706B			1706			1706G			Test
Parameter	Symbol	Min	Тур	Max	Unit	Conditions									
Supply Voltage	V <sub>S</sub> V+	±1.0 2.0		±5.0 10.0	V V	Dual Supply Single Supply									
Input Offset Voltage	V <sub>OS</sub>			0.9 1.7			2.0 2.8			4.5 5.3			10.0 11.0	mV mV	$R_S ≤ 100KΩ$ 0°C ≤ T <sub>A</sub> ≤ +70°C
Input Offset Current	I <sub>OS</sub>		0.1	25 240		0.1	25 240		0.1	25 240		0.1	30 450	pA pA	$T_{A} = 25^{\circ}C$ $0^{\circ}C \le T_{A} \le +70^{\circ}C$
Input Bias Current	IB		0.1	30 300		0.1	30 300		0.1	30 300		0.1	50 600	pA pA	$ \begin{array}{l} T_A \ = 25^\circC \\ 0^\circC \ \leq \ T_A \ \leq +70^\circC \end{array} \end{array} $
Input Voltage Range	V <sub>IR</sub>	-0.3 -2.8		5.3 2.8	V V	$V^+ = +5V$ $V_S = \pm 2.5V$									
Input Resistance	R <sub>IN</sub>		10 <sup>12</sup>		Ω										
Input Offset Voltage Drift	TCV <sub>OS</sub>		7			7			7			10		μV/°C	R <sub>S</sub> ≤ 100KΩ
Power Supply Rejection Ratio	PSRR	70 70	80 80		65 65	80 80		65 65	80 80		60 60	80 80		dB dB	$R_S ≤ 100KΩ$ 0°C ≤ T <sub>A</sub> ≤ +70°C
Common Mode Rejection Ratio	CMRR	70 70	83 83		65 65	83 83		65 65	83 83		60 60	83 83		dB dB	$R_S ≤ 100KΩ$ 0°C ≤ T <sub>A</sub> ≤ +70°C
Large Signal Voltage Gain	Av	32 20	100		32 20	100		32 20	100		20 10	80		V/ mV V/ mV	$R_L = 1M\Omega$ $R_L = 1M\Omega$ $0^{\circ}C \le T_A \le +70^{\circ}C$
Output Voltage		4.99	0.001 4.999	0.01	4.99	0.001 4.999	0.01	4.99	0.001 4.999	0.01	4.99	0.001 4.999	0.01	V V	$R_{L} = 1M\Omega$ $0^{\circ}C \le T_{A} \le +70^{\circ}C$
Range	V <sub>O</sub> low V <sub>O</sub> high	2.30	-2.40 2.40	-2.30	V V	$R_{L} = 100 K\Omega$ $0^{\circ}C \le T_{A} \le +70^{\circ}C$									
Output Short Circuit Current	I <sub>SC</sub>		200			200			200			200		μΑ	
Supply Current	IS		20	40		20	40		20	40		20	50	μΑ	V <sub>IN</sub> = 0V No Load
Power Dissipation	PD			200			200			200			250	μW	$V_S = \pm 2.5 V$

ALD1706A/ALD1706B ALD1706/ALD1706G

# **OPERATING ELECTRICAL CHARACTERISTICS (cont'd)**

			1706A			1706B			1706			1706G			Test
Parameter	Symbol	Min	Тур	Мах	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	Conditions
Input Capacitance	C <sub>IN</sub>		1			1			1			1		pF	
Bandwidth	BW		400			400			400			400		KHz	
Slew Rate	S <sub>R</sub>		0.17			0.17			0.17			0.17		V/µs	A <sub>V</sub> = +1 R <sub>L</sub> = 1MΩ
Rise time	tr		1.0			1.0			1.0			1.0		μS	R <sub>L</sub> = 1MΩ
Overshoot Factor			20			20			20			20		%	R <sub>L</sub> =1MΩ C <sub>L</sub> = 25pF
Settling Time	t <sub>s</sub>		10.0			10.0			10.0			10.0		μS	0.1% AV = -RL=1MΩ CL = 25pF

# $T_A = 25^{\circ}C$ $V_S = \pm 2.5V$ unless otherwise specified

## $T_A = 25^{\circ}C$ $V_S = \pm 1.0V$ unless otherwise specified

		1706A			1706B			1706		1	706G			Test	
Parameter	Symbol	Min	Тур	Мах	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	Conditions
Power Supply Rejection Ratio	PSRR		70			70			70			70		dB	R <sub>S</sub> ≤1MΩ
Common Mode Rejection Ratio	CMRR		70			70			70			70		dB	R <sub>S</sub> ≤ 1MΩ
Large Signal Voltage Gain	Av		50			50			50			50		V/ mV	$R_L = 1M\Omega$
Output Voltage Range	V <sub>O</sub> low V <sub>O</sub> high	0.9	-0.95 0.95	-0.9	0.9	-0.95 0.95	-0.9	0.9	-0.95 0.95	-0.9	0.9	-0.95 0.95	-0.9	V V	$R_L = 1M\Omega$
Bandwidth	BW		0.3			0.3			0.3			0.3		MHz	
Slew Rate	S <sub>R</sub>		0.17			0.17			0.17			0.17		V/µs	$A_V = +1$ $C_L = 25pF$

# $V_S = \pm 2.5V - 55^{\circ}C \le T_A \le +125^{\circ}C$ unless otherwise specified

			1706BDA			1706DA			Test
Parameter	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Conditions
Input Offset Voltage	V <sub>OS</sub>			3.0			6.5	mV	R <sub>S</sub> ≤ 100KΩ
Input Offset Current	los			8.0			8.0	nA	
Input Bias Current	Ι <sub>Β</sub>			10.0			10.0	nA	
Power Supply Rejection Ratio	PSRR	60	75		60	75		dB	R <sub>S</sub> ≤ 1MΩ
Common Mode Rejection Ratio	CMRR	60	83		60	83		dB	Rs≤1MΩ
Large Signal Voltage Gain	Av	15	50		15	50		V/ mV	R <sub>L</sub> = 1MΩ
Output Voltage Range	V <sub>O</sub> low V <sub>O</sub> high	2.30	-2.40 2.40	-2.30	2.30	-2.40 2.40	-2.30	V V	$R_L = 1M\Omega$

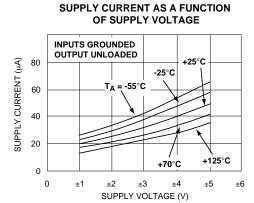
ALD1706A/ALD1706B ALD1706/ALD1706G Advanced Linear Devices

#### **Design & Operating Notes:**

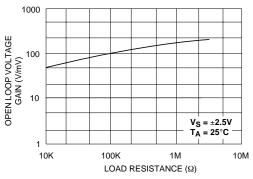
- 1. The ALD1706A/ALD1706B/ALD1706/ALD1706G CMOS operational amplifier uses a 3 gain stage architecture and an improved frequency compensation scheme to achieve large voltage gain, high output driving capability, and better frequency stability. In a conventional CMOS operational amplifier design, compensation is achieved with a pole splitting capacitor together with a nulling resistor. This method is, however, very bias dependent and thus cannot accommodate the large range of supply voltage operation as is required from a stand alone CMOS operational amplifier. The ALD1706A/ALD1706B/ALD1706/ALD1706G is internally compensated for unity gain stability using a novel scheme that does not use a nulling resistor. This scheme produces a clean single pole roll off in the gain characteristics while providing for more than 70 degrees of phase margin at the unity gain frequency.
- 2. The ALD1706A/ALD1706B/ALD1706/ALD1706G has complementary p-channel and n-channel input differential stages connected in parallel to accomplish rail-to-rail input common mode voltage range. This means that with the ranges of common mode input voltage close to the power supplies, one of the two differential stages is switched off internally. To maintain compatibility with other operational amplifiers, this switching point has been selected to be about 1.5V below the positive supply voltage. Since offset voltage trimming on the ALD1706A/ALD1706B/ALD1706/ALD1706G is made when the input voltage is symmetrical to the supply voltages, this internal switching does not affect a large variety of applications such as an inverting amplifier or non-inverting amplifier with a gain larger than 2.5 (5V operation), where the common mode voltage does not make excursions above this switching point. The user should however, be aware that this switching does take place if the operational amplifier is connected as a unity gain buffer and should make provision in his design to allow for input offset voltage variations.
- 3. The input bias and offset currents are essentially input protection diode reverse bias leakage currents, and are typically less than

1pA at room temperature. This low input bias current assures that the analog signal from the source will not be distorted by input bias currents. Normally, this extremely high input impedance of greater than  $10^{12}\Omega$  would not be a problem as the source impedance would limit the node impedance. However, for applications where source impedance is very high, it may be necessary to limit noise and hum pickup through proper shielding.

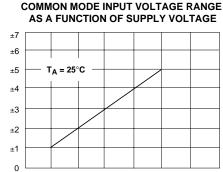
- 4. The output stage consists of class AB complementary output drivers, capable of driving a low resistance load. The output voltage swing is limited by the drain to source on-resistance of the output transistors as determined by the bias circuitry, and the value of the load resistor. When connected in the voltage follower configuration, the oscillation resistant feature, combined with the rail to rail input and output feature, makes an effective analog signal buffer for medium to high source impedance sensors, transducers, and other circuit networks.
- 5. The ALD1706A/ALD1706B/ALD1706/ALD1706G operational amplifier has been designed to provide full static discharge protection. Internally, the design has been carefully implemented to minimize latch up. However, care must be exercised when handling the device to avoid strong static fields that may degrade a diode junction, causing increased input leakage currents. In using the operational amplifier, the user is advised to power up the circuit before, or simultaneously with, any input voltages applied and to limit input voltages to not exceed 0.3V of the power supply voltage levels.
- 6. The ALD1706A/ALD1706B/ALD1706/ALD1706G, with its micropower operation, offers numerous benefits in reduced power supply requirements, less noise coupling and current spikes, less thermally induced drift, better overall reliability due to lower self heating, and lower input bias current. It requires practically no warm up time as the chip junction heats less than 0.1°C above ambient temperature under most operating conditions.





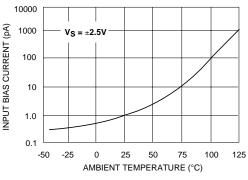


ALD1706A/ALD1706B ALD1706/ALD1706G



0 ±1 ±2 ±3 ±4 ±5 ±6 ±7 SUPPLY VOLTAGE (V)

#### INPUT BIAS CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE



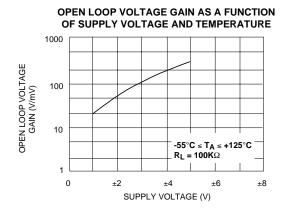
#### 4 of 9

# TYPICAL PERFORMANCE CHARACTERISTICS

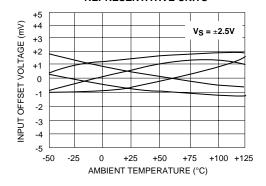
Advanced Linear Devices

COMMON MODE INPUT VOLTAGE RANGE (V)

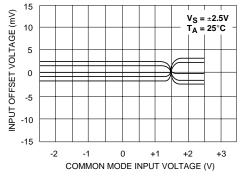
# **TYPICAL PERFORMANCE CHARACTERISTICS (cont'd)**



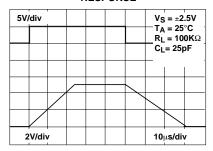




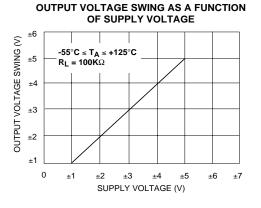




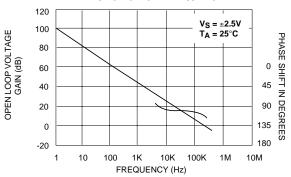
LARGE - SIGNAL TRANSIENT RESPONSE



ALD1706A/ALD1706B ALD1706/ALD1706G Advanced Linear Devices

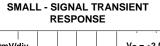


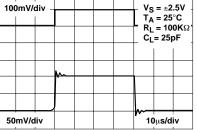




LARGE - SIGNAL TRANSIENT RESPONSE

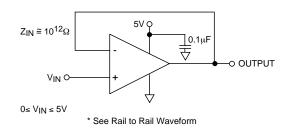
_ 2	2V/div					— T, — R	S = ± A = 2 L = 1 L = 2	5°C 00KΩ
						$\int$		
50	0mV	//div	J			1	0μ <b>s/c</b>	liv



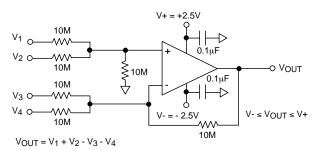


# **TYPICAL APPLICATIONS**

## RAIL-TO-RAIL VOLTAGE FOLLOWER/BUFFER

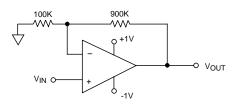


#### HIGH INPUT IMPEDANCE RAIL-TO-RAIL PRECISION DC SUMMING AMPLIFIER

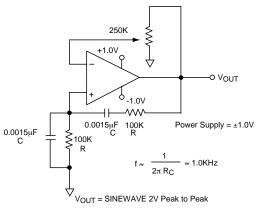


 $R_{IN} = 10M\Omega$  Accuracy limited by resistor tolerances and input offset voltage

#### HIGH IMPEDANCE NON-INVERTING AMPLIFIER

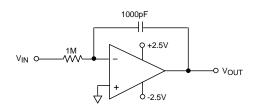


#### WIEN BRIDGE OSCILLATOR

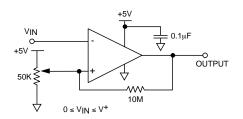


ALD1706A/ALD1706B ALD1706/ALD1706G

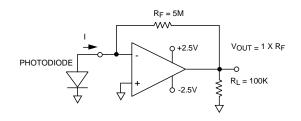
### **CHARGE INTEGRATOR**



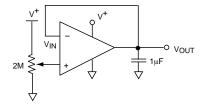
#### **RAIL-TO-RAIL VOLTAGE COMPARATOR**



#### PHOTO DETECTOR CURRENT TO VOLTAGE CONVERTER



#### MICROPOWER BUFFERED VARIABLE VOLTAGE SOURCE



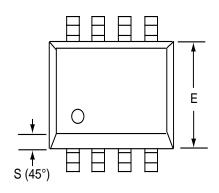
 $\begin{array}{l} 2.0V \leq V^{+} \leq 12.0V \\ 0.1 \leq V_{OUT} \leq (V^{+} - 0.1) \ V \\ OUPUT \ CURRENT \ \pm 200 \mu A \end{array}$ 

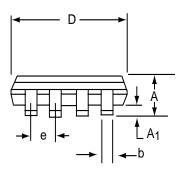
Advanced Linear Devices

6 of 9

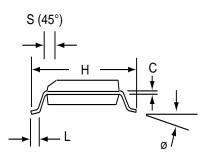
# **SOIC-8 PACKAGE DRAWING**

8 Pin Plastic SOIC Package





	Millim	neters	Inc	hes		
Dim	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.25	0.004	0.010		
b	0.35	0.45	0.014	0.018		
С	0.18	0.25	0.007	0.010		
D-8	4.69	5.00	0.185	0.196		
Е	3.50	4.05	0.140	0.160		
е	1.27	BSC	0.050 BSC			
н	5.70	6.30	0.224	0.248		
L	0.60	0.937	0.024	0.037		
Ø	0°	8°	0°	8°		
S	0.25	0.50	0.010	0.020		

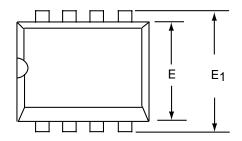


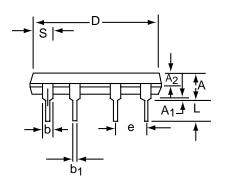
ALD1706A/ALD1706B
ALD1706/ALD1706G

Advanced Linear Devices

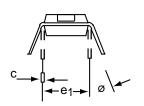
# **PDIP-8 PACKAGE DRAWING**

8 Pin Plastic DIP Package



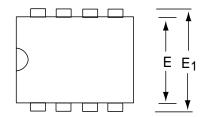


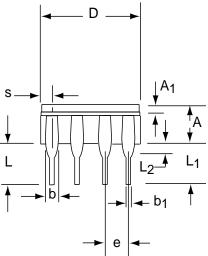
	Millin	neters	Inches			
Dim	Min	Max	Min	Max		
Α	3.81	5.08	0.105	0.200		
A <sub>1</sub>	0.38	1.27	0.015	0.050		
A <sub>2</sub>	1.27	2.03	0.050	0.080		
b	0.89	1.65	0.035	0.065		
b <sub>1</sub>	0.38	0.51	0.015	0.020		
С	0.20	0.30	0.008	0.012		
D-8	9.40	11.68	0.370	0.460		
Е	5.59	7.11	0.220	0.280		
E <sub>1</sub>	7.62	8.26	0.300	0.325		
е	2.29	2.79	0.090	0.110		
e <sub>1</sub>	7.37	7.87	0.290	0.310		
L	2.79	3.81	0.110	0.150		
S-8	1.02	2.03	0.040	0.080		
Ø	0°	15°	0°	15°		

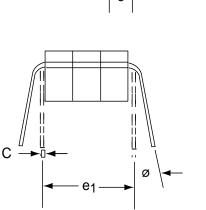


# **CERDIP-8 PACKAGE DRAWING**

# 8 Pin CERDIP Package







	Millim	neters	Inc	hes		
Dim	Min	Max	Min	Max		
Α	3.55	5.08	0.140	0.200		
A <sub>1</sub>	1.27	2.16	0.050	0.085		
b	0.97	1.65	0.038	0.065		
b <sub>1</sub>	0.36	0.58	0.014	0.023		
С	0.20	0.38	0.008	0.015		
D-8		10.29		0.405		
E	5.59	7.87	0.220	0.310		
E <sub>1</sub>	7.73	8.26	0.290	0.325		
е	2.54 E	BSC	0.100 BSC			
e <sub>1</sub>	7.62 E	BSC	0.300	BSC		
L	3.81	5.08	0.150	0.200		
L <sub>1</sub>	3.18		0.125			
L <sub>2</sub>	0.38	1.78	0.015	0.070		
S		2.49		0.098		
ø	0°	15°	0°	15°		

ALD1706A/ALD1706B ALD1706/ALD1706G